



General Description:

- (1) Chip Dimension
 Chip Size= 12 mil x 13 mil (300um x 330um)
 Chip Thickness = 90±10µm
 P/N Bonding Pad = 90±5µm
- (2) Electrode:
 P (Anode) → Au
 N (Cathode) → Au
- (3) Structure:
 Refer to drawing
 SiO₂ Passivated surface

Electro-optical Characteristics(Ta=RT)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Forward Voltage	V _F	2.8	3.3	3.5	V	I _F =20mA
Dominant Wavelength	λ _D	450	460	475	nm	I _F =20mA
Reverse Current	I _R	0	-	1	µA	V _R =-5V

Luminous Intensity(I _V) mcd at I _F =20mA	Dominant Wavelength(nm)							
	Range	447.5~450	450~452.5	452.5~455	455~457.5	457.5~460	460~462.5	462.5~465
80~90	*	*						
90~100	*	*	*					
100~120		*	*	*				
120~140		*	*	*	*			
140~160			*	*	*	*		
160~180				*	*	*	*	*
180~200					*	*	*	*
200~220						*	*	*

Features:

- 1. High Luminous Intensity
- 2. Long Operation Life
- 3. High Current; Pulse Operation
- 4. Indoor/Outdoor Applications

Notes:

- 1. Dominant wavelength includes an error of ± 1nm
- 2. Luminous intensity includes an error of ±10%
- 3. Luminous intensity is measured on bare chip
- 4. InGaN LED is sensitive to ESD